

Application No. 09/160,657

comprised of a material selected from the group consisting of:  
a Group IV element and gallium arsenide.

77. (Amended) A semiconductor device according to claim 81 wherein the semiconductive layer comprises silicon, and the gate insulating film includes a silicon compound.

**REMARKS:**

Claims 40, 42-45, 47, 48, 62, 64, 66-68, 70, 71 and 72-76 have been cancelled and claims 41, 46, 47, 60, 61, 63, 65, 69, 72 and 77 have been amended. No new claims have been added. Consideration is requested.

The allowance of claims 79-81 has been noted with appreciation.

The amendments presented herein serve to change claim dependencies so that the amended claims depend on claim(s) that have been allowed and, in the case of amended claim 77, to change the word "dielectric" to - -insulating- - for consistency with the recitation in claim 81 from which it now depends. No additional search or examination effort should be required as a result of the amendments and all claims pending in the application should be in condition for allowance. Consequently, entry of the amendment is believed proper and is solicited.

**CONCLUSION:**

It is believed this amendment places the application in order for allowance without additional search or examination being required. Early allowance of the application will be appreciated.

If after consideration, the Examiner believes that any outstanding matters remain, a telephone call to the undersigned attorney at 972-702-7940 will be

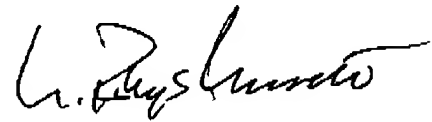
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appreciated.

Attached hereto is a marked up version of the changes made to the specification and claims by the current amendment. The attached page is captioned "**Version with markings to show changes made.**"

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Respectfully submitted,



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**VERSION WITH MARKINGS TO SHOW CHANGES MADE**

**In the claims:**

Claims 40, 42-45, 47, 48, 62, 64, 66-68, 70, 71 and 72-76 have been cancelled.

The following claims have been amended as shown:

41. (Twice Amended) The semiconductor device of claim ~~40~~79 wherein said gate insulating layer comprises silicon dioxide.

46. (Amended) The semiconductor device of claim ~~40~~80, comprising deuterium atoms from said post-fabrication passivation covalently bonded at said interface.

47. (Amended) The semiconductor device of claim ~~40~~81, which is encapsulated.

60. (Twice Amended) The semiconductor device of claim ~~40~~80, wherein said gate insulating layer comprises an oxide of silicon.

61. (Twice Amended) The semiconductor device of claim ~~40~~81, wherein said gate insulating layer comprises silicon dioxide or silicon oxy nitride.

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63. (Twice Amended) The semiconductor device of claim ~~62-80~~, wherein said gate insulating layer comprises silicon dioxide.

65. (Amended) The semiconductor device of claim ~~6280~~, comprising deuterium atoms from said post-fabrication passivation covalently bonded at said interface.

69 (Twice Amended) The device as recited in claim ~~68-81~~, wherein said transistor gate is comprised of polycrystalline silicon.

72. (Twice Amended) The device as recited in claim ~~66-81~~ wherein said substrate is comprised of a material selected from the group consisting of:  
a Group IV element and gallium arsenide.

77. (Amended) A semiconductor device according to claim ~~76-81~~ wherein the semiconductive layer comprises silicon, and the gate ~~dielectric~~ insulating film includes a silicon compound.

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE****Certificate of Facsimile Transmission under 37 CFR 1.8**

In re Application No. 09/160,657

Group Art Unit: 2822

Filed: 09/25/1998

Inventor: LYDING, J. et al

Examiner: VOCKRODT, Jeff B.

For: Semiconductive Devices and Methods for same

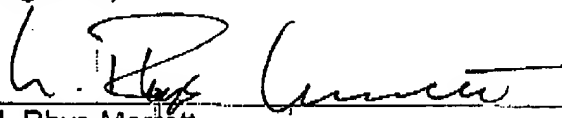
Fax No. 703-872-9319

**(7 PAGES TOTAL)**

I hereby certify that the below correspondence is being facsimile transmitted to the United States Patent Office on September 23, 2002.

- Amendment under 37 CFR 1.116 (6) pages)

(Signature)

  
N. Rhys Merrett**FAX COPY RECEIVED**

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(Date)

23 September 2002

**PLEASE DELIVER IMMEDIATELY TO:****Examiner JEFF B. VOCKRODT****ART UNIT 2882****AMENDMENT AFTER FINAL**

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